

ABSTRACT

The present invention relates to a method of producing an SOI wafer in which an SOI layer is formed on a buried oxide film by forming an oxide film on a surface of at least one of a bond wafer and a base wafer, bonding the bond wafer to the base wafer through the formed oxide film, and making the bond wafer into a thin film, wherein after the oxide film is formed so that a total thickness of the oxide film formed on the surface of at least one of the bond wafer and the base wafer is thicker than a thickness of the buried oxide film that the SOI wafer to be produced has, the bond wafer is bonded to the base wafer through the formed oxide film, the bond wafer is made into a thin film to form an SOI layer, and thereafter, an obtained bonded wafer is subjected to heat treatment to reduce a thickness of the buried oxide film. Thereby, there can be provided a method of producing an SOI wafer in which blisters and voids are not generated even if the thickness of the buried oxide film is thinned, and its SOI layer has extremely good crystallinity.